

# Modeling I/O Buffers

(Part 1)

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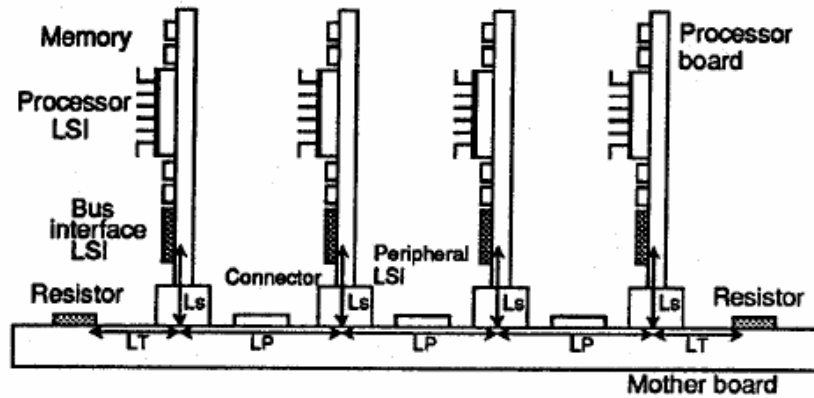
## Outline

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- Buffers driving transmission lines
- Types of buffer models
- Transistor-level models
- Transistor-level models: ECL techniques
- Transistor-level models: GTL techniques

## Buffers Driving Transmission Lines

Example of a multiprocessor system

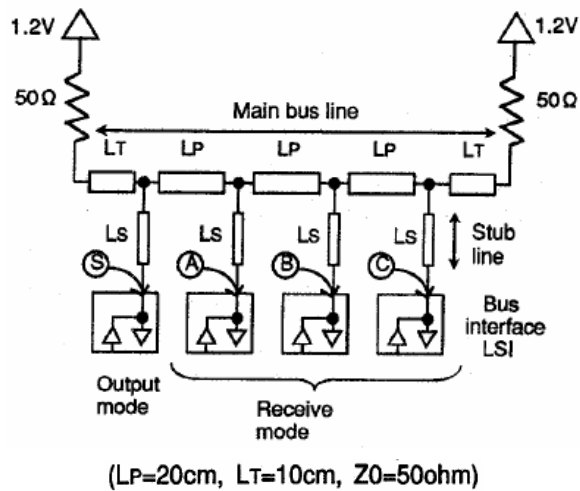


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(Kudoh, 1995) <sub>3</sub>

## Buffers Driving Transmission Lines (cont)

Bus model of the multiprocessor system



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## Types of Buffer Models for Digital Design

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- Linear models
- Nonlinear behavioral models
- Detailed electrical models (transistor level)

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## Transistor Level Models

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- ☺ Advantages
  - Accuracy
- ☹ Drawbacks
  - Relatively high computational cost during simulation
  - Detailed models are difficult to find (proprietary info)
- Requirements
  - I/O circuit schematic or netlist (text file)
  - Technology process files (foundry)
  - Device dimensions
- Sources of information
  - Component suppliers (databooks, SPICE models)
  - Model libraries from CAD tools

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## Transistor Level Models – ECL Drivers

- ECL technology allows very high-speed switching
- As oppose to TTL, ECL transistors are not allow to saturate
- ECL buffering techniques are enjoying renewed popularity due to the availability of BiCMOS IC process technology

ECL 10K AND 100K LOGIC

	MECL 10K	Fairchild 100K
$V_{OH(max)}$ (V)	-0.81	-0.88
$V_{OH(min)}$ (V)	-0.96	-1.03
$V_{OL(max)}$ (V)	-1.65	-1.62
$V_{OL(min)}$ (V)	-1.85	-1.81

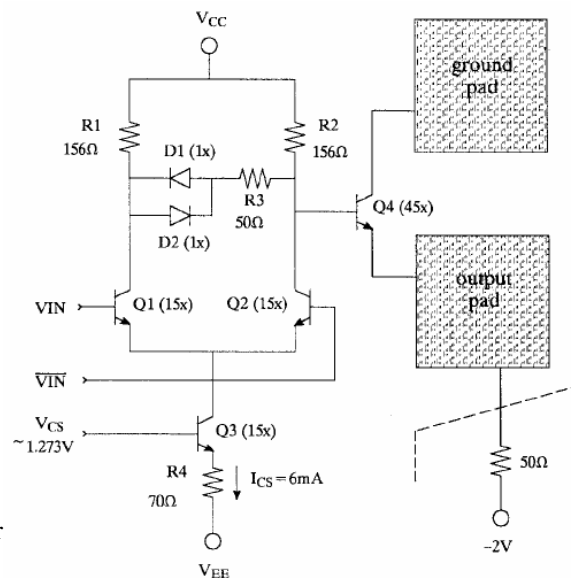
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(Lefebvre, 1997)

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## Transistor Level Models – ECL Drivers (cont)

### ECL Output Driver



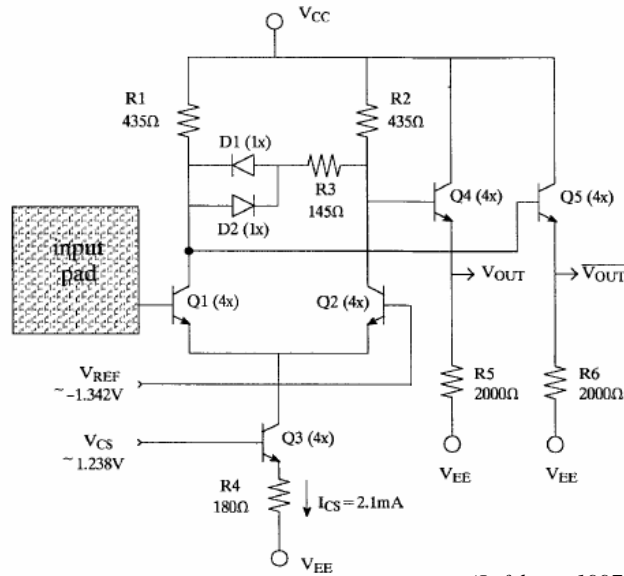
( $D_1$ ,  $D_2$  and  $R_3$  are used for temperature compensation)

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(Lefebvre, 1997) 8

## Transistor Level Models – ECL Drivers (cont)

### ECL Input Driver



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(Lefebvre, 1997)

## Transistor Level Models – ECL Drivers (cont)

Major drawback of ECL techniques: power consumption

Logic level	Power (Watts)	Termination (both ends)
ECL	20	50Ω to 3.0V
BTL	11	50Ω to 2.0V
GTL	1.5	50Ω to 1.2V

**Table 1: Estimated nominal power for 160 active I/O drivers.**

(Gunning, 1992)

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## Transistor Level Models – GTL Drivers

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- GTL uses CMOS process technology (low power consumption and low fabrication cost)
- Essentially, the drivers are open drain NMOS common source stages, and the receivers are NMOS differential amplifiers

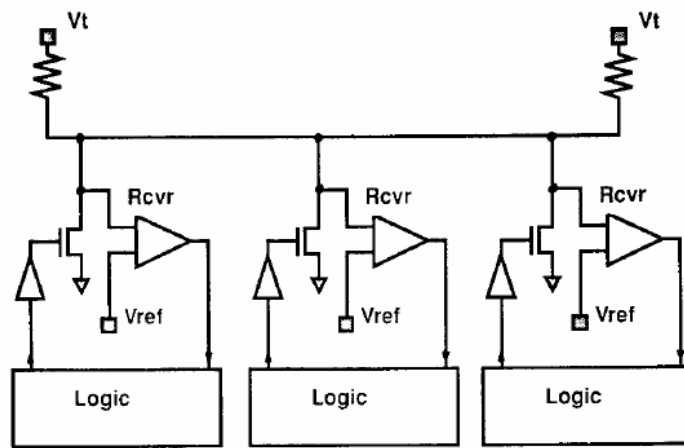
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## Transistor Level Models – GTL Drivers (cont)

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I/O Transceivers in a bidirectional transmission line bus



(the transmission line is terminated at both ends)

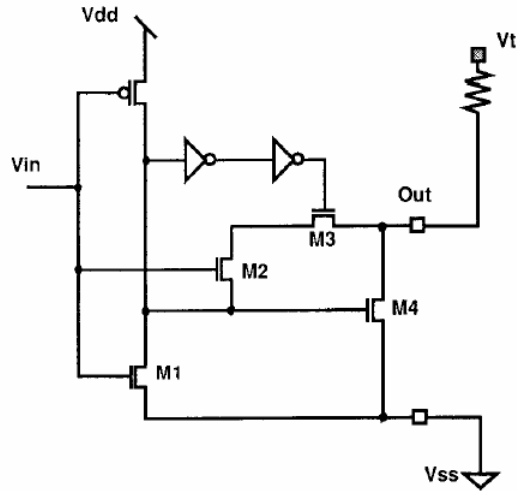
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(Gunning, 1992) 12

## Transistor Level Models – GTL Drivers (cont)

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### Output driver (transmitter)



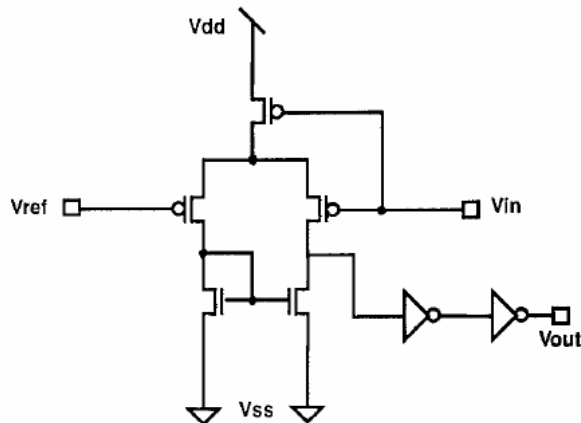
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(Gunning, 1992) 13

## Transistor Level Models – GTL Drivers (cont)

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### Input buffer (receiver)

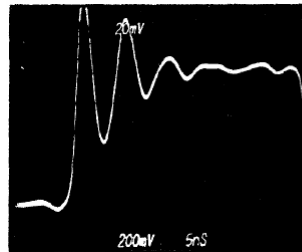
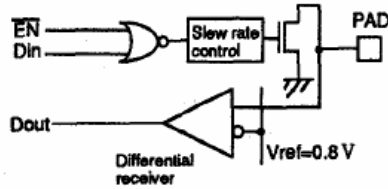


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(Gunning, 1992) 14

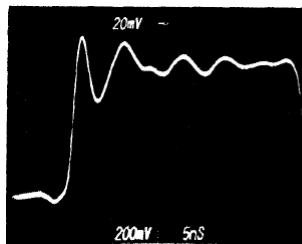
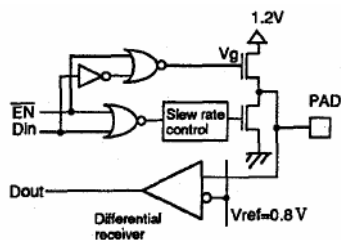
## Transistor Level Models – GTL Drivers (cont)

### Open drain MOS output driver



Vref = 0.80V  
Undershoot = 0.72V

### Push-pull MOS output driver



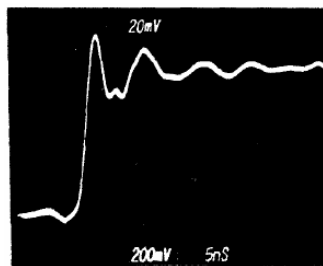
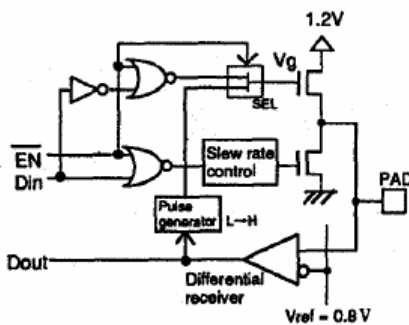
Undershoot = 0.96V  
Vref = 0.80V

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(Kudoh, 1995)<sub>15</sub>

## Transistor Level Models – GTL Drivers (cont)

### Push-pull MOS output driver with dynamic termination



Undershoot = 1.05V  
Vref = 0.80V

(In receive mode, the pull-up NMOS transistor acts as a dynamic resistance to compensate the undershoot)

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(Kudoh, 1995)<sub>16</sub>